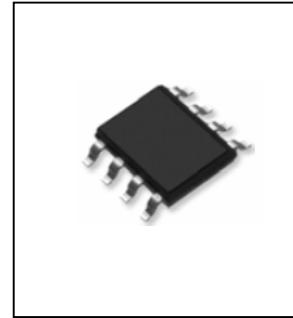


## P-Channel MOSFET

### DESCRIPTION

The SL4459 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.



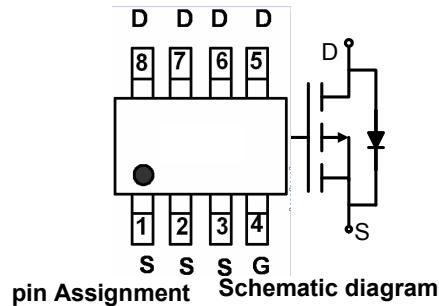
SOP-8 top view

### GENERAL FEATURES

- $V_{DS} = -30V, I_D = -6.5A$
- $R_{DS(ON)} < 46m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} < 72m\Omega @ V_{GS}=-4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

### Application

- PWM applications
- Load switch
- Power management



### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-6.5	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-22	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	°C/W
--	-----------------	----	------

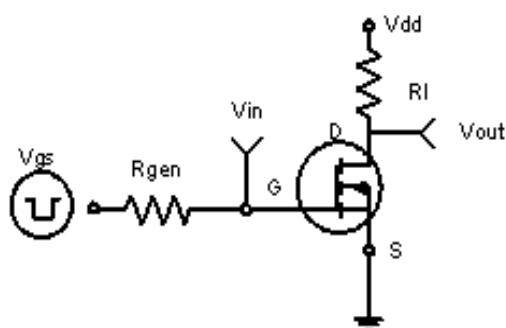
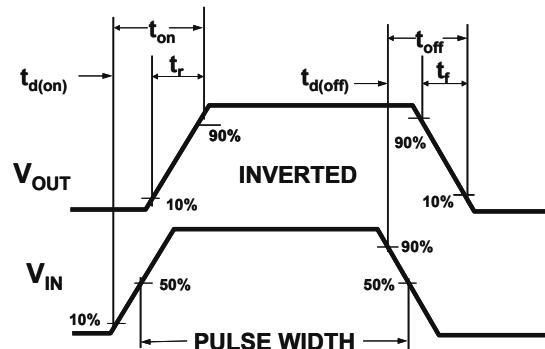
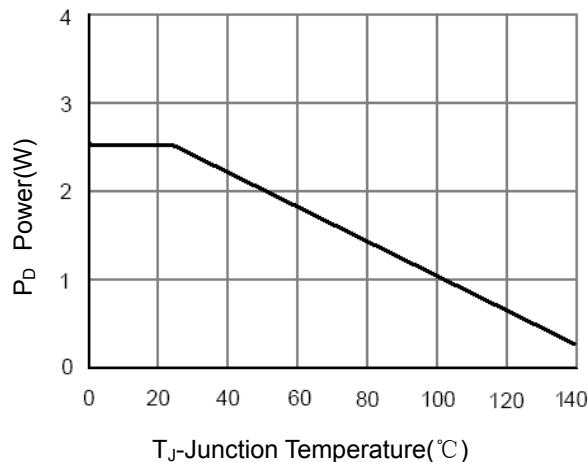
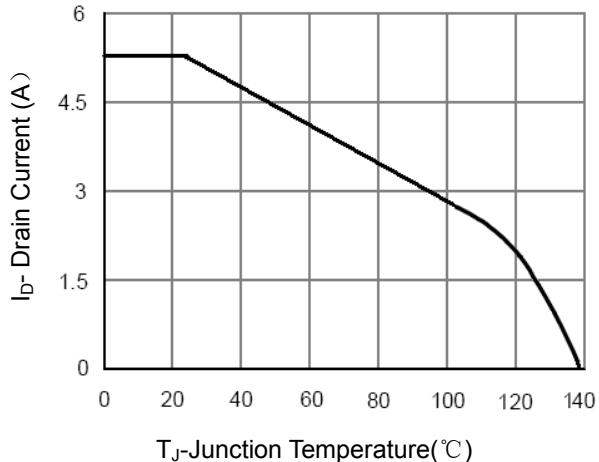
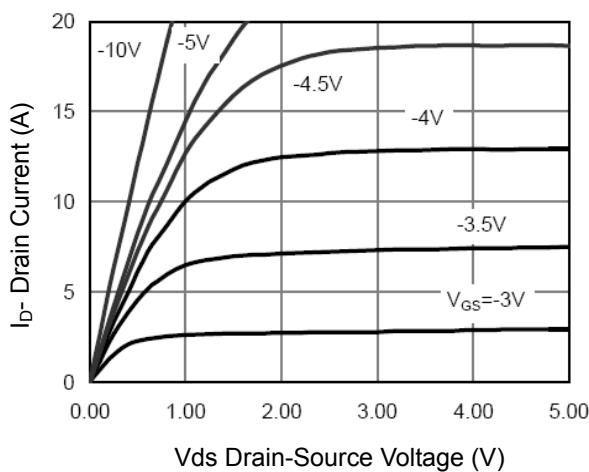
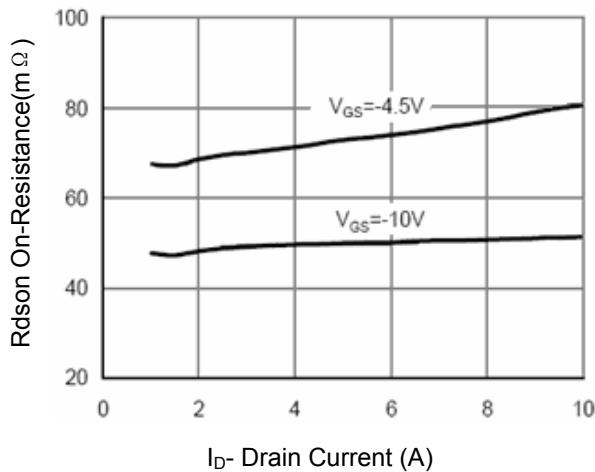
### Electrical Characteristics (TA=25°C unless otherwise noted)

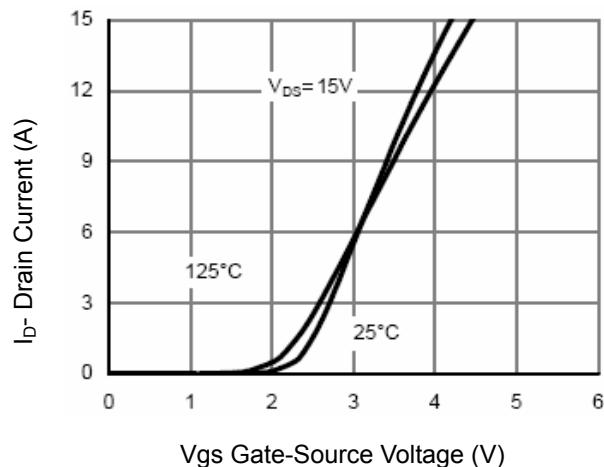
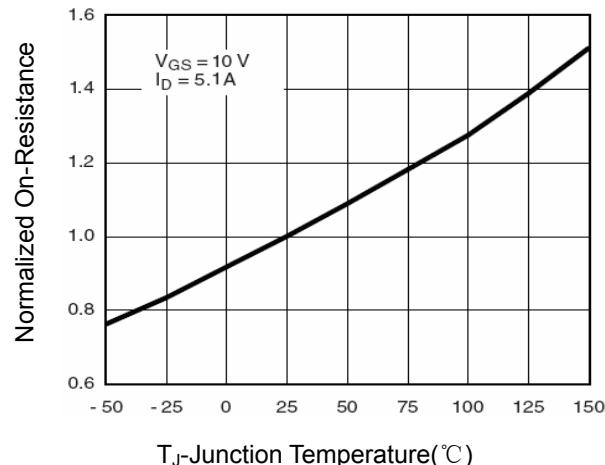
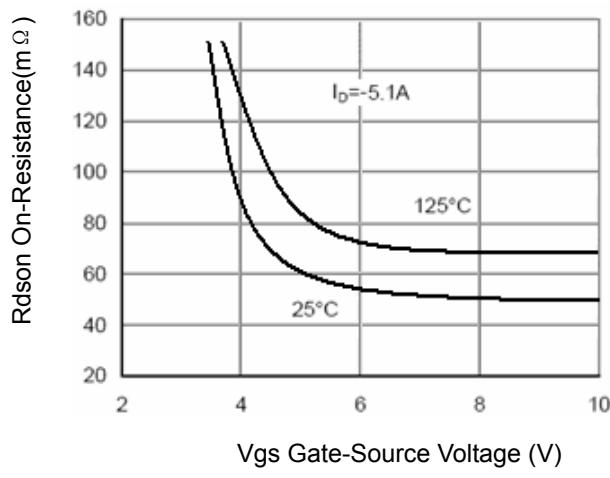
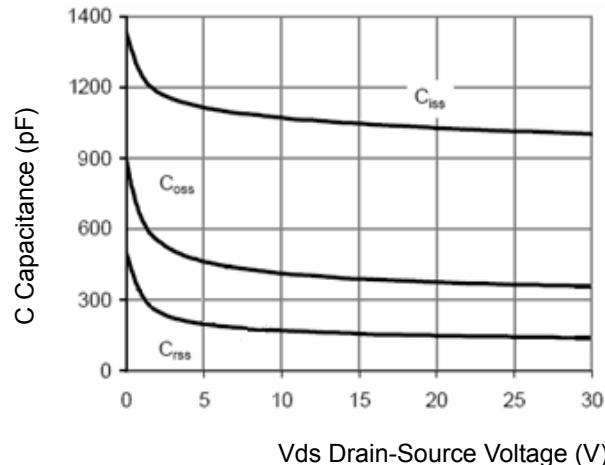
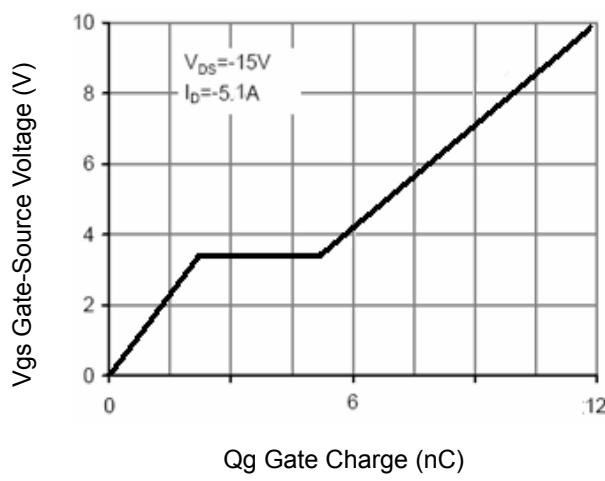
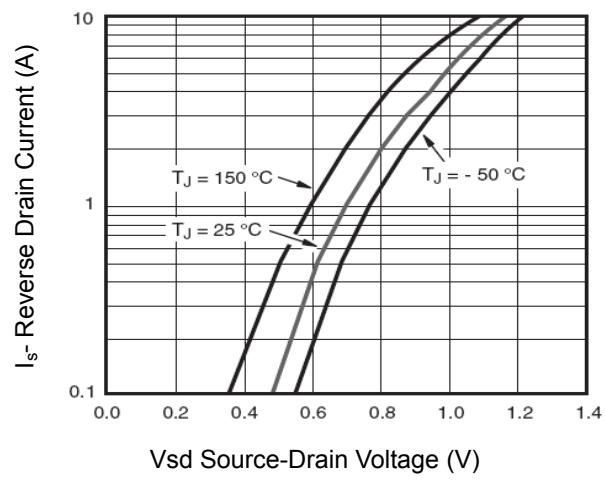
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V I_D=-250\mu A$	-30	-33		V

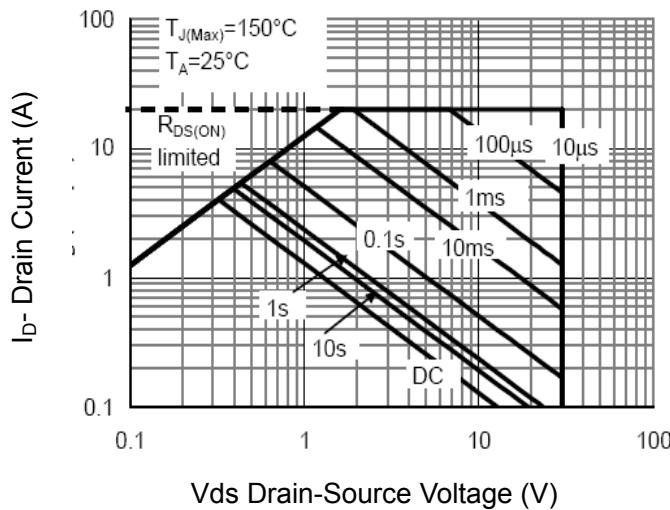
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1		-2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-6A$			46	$m\Omega$
		$V_{GS}=-6V, I_D=-5A$			58	$m\Omega$
		$V_{GS}=-4.5V, I_D=-5A$			72	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-6.5A$	4	7		S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V, F=1.0MHz$		1040		PF
Output Capacitance	$C_{oss}$			420		PF
Reverse Transfer Capacitance	$C_{rss}$			150		PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, ID=-1A, V_{GS}=-10V, R_{GEN}=6\Omega$		15		nS
Turn-on Rise Time	$t_r$			13		nS
Turn-Off Delay Time	$t_{d(off)}$			58		nS
Turn-Off Fall Time	$t_f$			21		nS
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-6.5A, V_{GS}=-10V$		12		nC
Gate-Source Charge	$Q_{gs}$			2.2		nC
Gate-Drain Charge	$Q_{gd}$			3		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-1.7A$			-1.2	V

**Notes:**

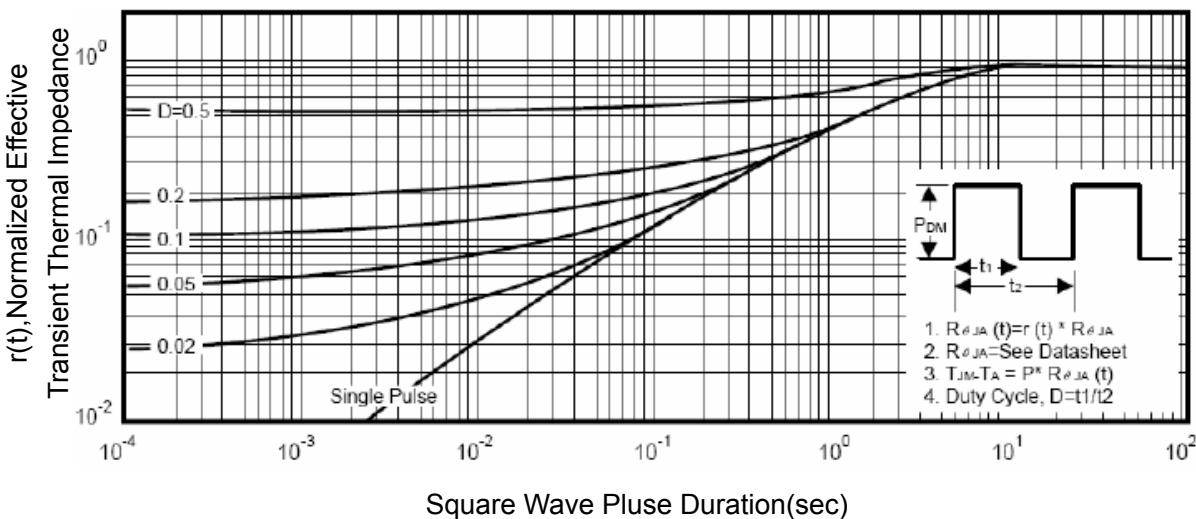
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS****Figure 1:Switching Test Circuit****Figure 2:Switching Waveforms****Figure 3 Power Dissipation****Figure 4 Drain Current****Figure 5 Output CHARACTERISTICS****Figure 6 Drain-Source On-Resistance**

**Figure 7 Transfer Characteristics****Figure 8 Drain-Source On-Resistance****Figure 9 Rdson vs Vgs****Figure 10 Capacitance vs Vds****Figure 11 Gate Charge****Figure 12 Source- Drain Diode Forward**

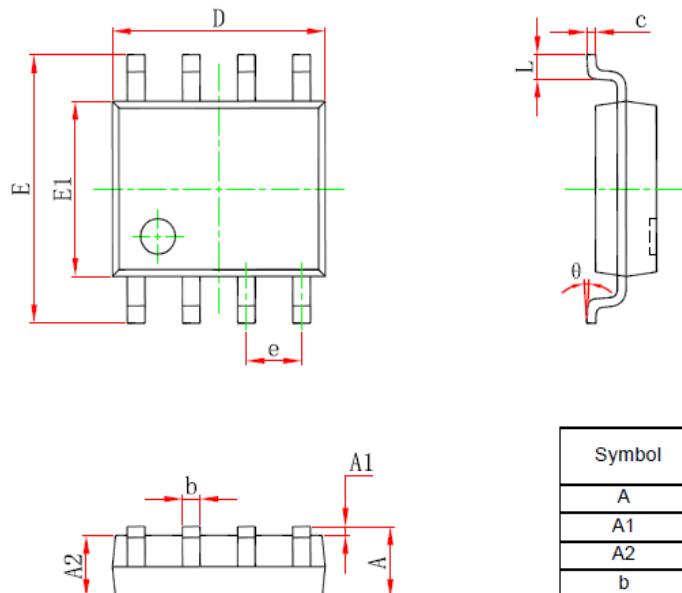


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

## SOP-8 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°